

IR2131(J)(S) & (PbF)

3 HIGH SIDE AND 3 LOW SIDE DRIVER

Features

- Floating channel designed for bootstrap operation Fully operational to +600V Tolerant to negative transient voltage dV/dt immune
- · Gate drive supply range from 10 to 20V
- Undervoltage lockout for all channels
- Over-current shutdown turns off all six drivers
- Independent 3 high side & 3 low side drivers
- · Matched propagation delay for all channels
- 2.5V logic compatible
- · Outputs out of phase with inputs
- 28-Lead SOIC & 44-Lead PLCC are also available in Lead-Free.

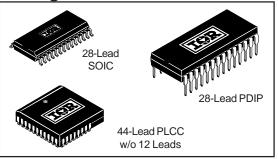
Description

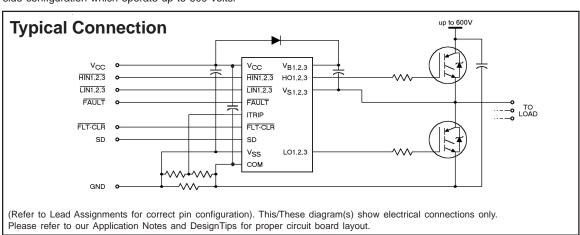
The IR2131(J)(S) is a high voltage, high speed power MOSFET and IGBT driver with three independent high and low side referenced output channels. Proprietary HVIC technology enables ruggedized monolithic construction. Logic inputs are compatible with CMOS or LSTTL outputs, down to 2.5V logic. A current trip function which terminates all six outputs can be derived from an external current sense resistor. A shutdown input is provided for a customized shutdown function. An open drain FAULT signal is provided to indicate that any of the shutdowns has occurred. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. Propagation delays are matched to simplify use in high frequency applications. The floating channels can be used to drive N-channel power MOSFETs or IGBTs in the high side configuration which operate up to 600 volts.

Product Summary

Voffset	600V max.
I _O +/-	160 mA / 360 mA
V _{OUT}	10 - 20V
ton/off (typ.)	1.3 & 0.6 µs
Deadtime (typ.)	700 ns

Packages





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International

TOR Rectifier

Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions. Additional Information is shown in Figures 7 through 10.

Symbol	Definition		Min.	Max.	Units
V _{B1,2,3}	High Side Floating Supply Voltage		-0.3	625	
V _{S1,2,3}	High Side Floating Offset Voltage		V _{B1,2,3} - 25	$V_{B1,2,3} + 0.3$	
V _{HO1,2,3}	High Side Floating Output Voltage		V _{S1,2,3} - 0.3	$V_{B1,2,3} + 0.3$	
V _{CC}	Low Side and Logic Fixed Supply Voltage		-0.3	25	
V _{SS}	Logic Ground		V _{CC} - 25	V _{CC} + 0.3	
V _{LO1,2,3}	Low Side Output Voltage		-0.3	V _{CC} + 0.3	V
V _{IN}	Logic Input Voltage (HIN1,2,3, LIN1,2,3, FL	T-CLR, SD&ITRIP)	V _{SS} - 0.3	(V _{SS} + 15) or	
				(V _{CC} + 0.3) whichever	
				is lower	
V_{FLT}	FAULT Output Voltage		V _{SS} - 0.3	V _{CC} + 0.3	
dV _S /dt	Allowable Offset Supply Voltage Transient		_	50	V/ns
P _D	Package Power Dissipation @ T _A ≤+25°C	(28 Lead DIP)	_	1.5	
		(28 Lead SOIC)	_	1.6	W
		(44 Lead PLCC)	_	2.0	
Rth _{JA}	Thermal Resistance, Junction to Ambient	(28 Lead DIP)	_	83	
		(28 Lead SOIC)	_	78	°C/W
		(44 Lead PLCC)		63	°C
TJ	Junction Temperature		_	150	
T _S	Storage Temperature		-55	150	
TL	Lead Temperature (Soldering, 10 seconds)		_	300	

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. All voltage parameters are absolute voltages referenced to COM. The V_S offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
V _{B1,2,3}	High Side Floating Supply Voltage	V _{S1,2,3} + 10	V _{S1,2,3} + 20	
V _{S1,2,3}	High Side Floating Offset Voltage	Note 1	600	
V _{HO1,2,3}	High Side Floating Output Voltage	V _{S1,2,3}	V _{B1,2,3}	
V _{CC}	Low Side and Logic Fixed Supply Voltage	10	20	\/
V_{SS}	Logic Ground	-5	5	V
V _{LO1,2,3}	Low Side Output Voltage	0	Vcc	
V_{IN}	Logic Input Voltage (HIN1,2,3, LIN1,2,3, FLT - CLR, SD & ITRIP)	V_{SS}	V _{SS} + 5	
V_{FLT}	FAULT Output Voltage	V _{SS}	V _{CC}	
T _A	Ambient Temperature	-40	125	°C

Note 1: Logic operational for V_S of -5V to +600V. Logic state held for V_S of -5V to -V_{BS}. (Please refer to the Design Tip DT97-3 for more details).

Note 2: All input pins, CA- and CAO pins are internally clamped with a 5.2V zener diode.

Dynamic Electrical Characteristics

 $V_{BIAS}\left(V_{CC},V_{BS1,2,3}\right)=15V,V_{S1,2,3}=V_{SS}=COM,C_{L}=1000~pF~and~T_{A}=25^{\circ}C~unless~otherwise~specified.~The~dynamic~electrical~characteristics~are~defined~in~Figures~4~through~5.$

	Parameter		Value			
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
t _{on}	Turn-On Propagation Delay	0.6	1.3	2.0	μs	
t _{off}	Turn-Off Propagation Delay	0.2	0.6	1.0	μο	$V_{IN} = 0 \& 5V$
t _r	Turn-On Rise Time	_	80	150		$V_{S1,2,3} = 0$ to 600V
t _f	Turn-Off Fall Time	—	40	100		
t _{itrip}	ITRIP to Output Shutdown Propagation Delay	400	700	1000		V _{IN} , V _{ITRIP} = 0 & 5V
t _{bl}	ITRIP Blanking Time	_	400	_		V _{ITRIP} = 1V
t _{flt}	ITRIP to FAULT Indication Delay	400	700	1000	ns	V _{IN} , V _{ITRIP} = 0 & 5V
t _{flt,in}	Input Filter Time (All Six Inputs)	_	310	_		V _{IN} = 0 & 5V
t _{fltclr}	FLT-CLR to FAULT Clear Time	400	800	1200		V_{IN} , V_{IT} , $V_{FC} = 0$
t _{sd}	SD to Output Shutdown Propagation Delay	400	700	1000		$V_{IN}, V_{SD} = 0 \& 5V$
DT	Deadtime	400	700	1200		V _{IN} = 0 & 5V

NOTE: For high side PWM, HIN pulse width must be $\geq 1.5 \mu sec$

Static Electrical Characteristics

 V_{BIAS} (V_{CC}, $V_{BS1,2,3}$) = 15V, $V_{S1,2,3}$ = V_{SS} = COM and T_A = 25°C unless otherwise specified. The V_{IN} , V_{TH} and I_{IN} parameters are referenced to V_{SS} and are applicable to all six logic input leads: $\overline{HIN1,2,3}$ & $\overline{LIN1,2,3}$. The V_O and I_O parameters are referenced to COM and $V_{S1,2,3}$ and are applicable to the respective output leads: HO1,2,3 or LO1,2,3.

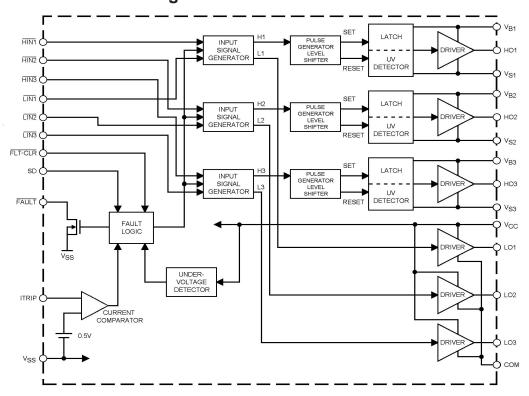
	Parameter		Value			
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
V _{IH}	Logic "0" Input Voltage (OUT = LO)	2.2	_	_		
V _{IL}	Logic "1" Input Voltage (OUT = HI)	_	_	0.8		
V _{FCLR,IH}	Logic "0" Fault Clear Input Voltage	2.2	_	_	V	
V _{FCLR,IL}	Logic "1" Fault Clear Input Voltage	_	_	0.8	V	
V _{SD,TH+}	Shutdown Input Positive Going Threshold	1.2	1.8	2.1		
V _{SD,TH-}	Shutdown Input Negative Going Threshold	0.9	1.5	1.8		
V _{IT,TH+}	ITRIP Input Positive Going Threshold	250	485	600		
V _{IT,TH-}	ITRIP Input Negative Going Threshold	200	400	550	mV	
VoH	High Level Output Voltage, VBIAS - VO	_	_	100	IIIV	$V_{IN} = 0V$, $I_O = 0A$
V _{OL}	Low Level Output Voltage, VO	_	_	100		$V_{IN} = 5V, I_{O} = 0A$
I_{LK}	Offset Supply Leakage Current	_	_	50		$V_{B} = V_{S} = 600V$
I _{QBS}	Quiescent V _{BS} Supply Current	_	30	100	μA	$V_{IN} = 0V \text{ or } 5V$
I _{QCC}	Quiescent V _{CC} Supply Current	_	3.0	4.5	mA	$V_{IN} = 0V \text{ or } 5V$
I _{IN+}	Logic "1" Input Bias Current (OUT = HI)	_	190	300		$V_{IN} = 0V$
I _{IN-}	Logic "0" Input Bias Current (OUT = LO)	_	50	100	μA	$V_{IN} = 5V$
I _{ITRIP+}	"High" ITRIP Bias Current	_	75	150		ITRIP = 5V
I _{ITRIP} -	"Low" ITRIP Bias Current	_	_	100	nA	ITRIP = 0V
I _{FCLR+}	Logic "1" Fault Clear Bias Current	_	125	250		FLT-CLR = 0V
I _{FCLR} -	Logic "0" Fault Clear Bias Current	_	75	150	μA	FLT-CLR = 5V
I _{SD+}	Logic "1" Shutdown Bias Current		75	150		SD = 5V
I _{SD} -	Logic "0" Shutdown Bias Current	_	_	100	nA	SD = 0V

Static Electrical Characteristics -- Continued

 V_{BIAS} (V_{CC} , $V_{BS1,2,3}$) = 15V, $V_{S1,2,3}$ = V_{SS} = COM and T_A = 25°C unless otherwise specified. The V_{IN} , V_{TH} and I_{IN} parameters are referenced to V_{SS} and are applicable to all six logic input leads: $\overline{HIN1,2,3}$ & $\overline{LIN1,2,3}$. The V_O and I_O parameters are referenced to COM and $V_{S1,2,3}$ and are applicable to the respective output leads: HO1,2,3 or LO1,2,3.

	Parameter		Value			
Symbol	Definition	Min.	Тур.	Max.	Units	Test Conditions
V _{BSUV+}	V _{BS} Supply Undervoltage Positive Going Threshold	8.2	8.7	9.2		
V _{BSUV} -	V _{BS} Supply Undervoltage Negative Going Threshold	7.8	8.3	8.8	V	
V _{CCUV+}	V _{CC} Supply Undervoltage Positive Going Threshold	8.2	8.7	9.2	V	
V _{CCUV} -	V _{CC} Supply Undervoltage Negative Going Threshold	7.8	8.3	8.8		
R _{on,FLT}	FAULT Low On-Resistance	—	55	75	Ω	
I _{O+}	Output High Short Circuit Pulsed Current	160	250	_	mA	$V_O = 0V, V_{IN} = 0V$ PW $\leq 10 \mu s$
I _{O-}	Output Low Short Circuit Pulsed Current	360	500	_	ША	$V_{O} = 15V, V_{IN} = 5V$ PW \le 10 \mus

Functional Block Diagram



Lead Definitions

Lea	ad
Symbol	Description
HIN1,2,3	Logic inputs for high side gate driver outputs (HO1,2,3), out of phase
LIN1,2,3	Logic inputs for low side gate driver output (LO1,2,3), out of phase
FLT-CLR	Logic input for fault clear
SD	Logic input for shutdown
FAULT	Indicates over-current or undervoltage lockout (low side) has occurred, negative logic
Vcc	Low side and logic fixed supply
ITRIP	Input for over-current shutdown
Vss	Logic ground
V _{B1,2,3}	High side floating supplies
HO1,2,3	High side gate drive outputs
V _{S1,2,3}	High side floating supply returns
LO1,2,3	Low side gate drive outputs
COM	Low side return

Lead Assignments

